

# VMMK-3313

15 - 33 GHz Directional Detector in SMT Package



## Data Sheet



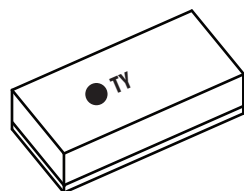
Lead (Pb) Free  
RoHS 6 fully  
compliant



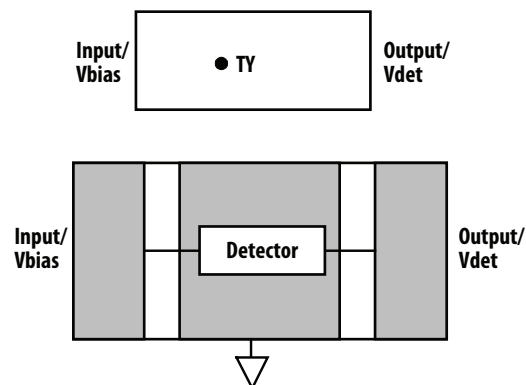
### Description

The VMMK-3313 is a small and easy-to-use, broadband, directional detector operating in various frequency bands from 15 to 33 GHz with typical insertion loss of 0.5 dB. It is housed in the Avago Technologies' industry-leading and revolutionary sub-miniature chip scale package (GaAsCap wafer scale leadless package) which is small and ultra thin yet can be handled and placed with standard 0402 pick and place assembly equipment. The VMMK-3313 provides a wide detecting power level from -5 to +30 dBm with excellent input and output return losses. A typical of 15 dB directivity is provided, and the detector requires only 1.5 V DC biasing with small current drawn of 0.17 mA.

**WLP0402, 1 mm x 0.5 mm x 0.25 mm**



### Pin Connections (Top View)



Note:  
"T" = Device Code  
"Y" = Month Code

### Features

- 1 x 0.5 mm surface mount package
- Ultrathin (0.25 mm)
- Wide frequency range: 15 to 33 GHz
- Wide dynamic range
- Low Insertion loss
- Directivity: 11-18 dB typ.
- In and output match: 50 ohm

### Specifications (24 GHz, Vb = 1.5 V, Zin = Zout = 50 Ω)

- Bias Current: 0.17 mA typical
- Insertion Loss: 0.5 dB
- Detector output offset voltage: 62 mV typical
- Detector Output voltage at +20 dBm: 1070 mV typical

### Applications

- Point-to-Point Radio
- Monitoring Power Amplifier Output Power
- Power Control Loop Detector



**Attention: Observe precautions for handling electrostatic sensitive devices.**  
ESD Machine Model = 70 V  
ESD Human Body Model = 350 V  
Refer to Avago Application Note A004R:  
Electrostatic Discharge, Damage and Control.

## Electrical Specifications

**Table 1. Absolute Maximum Rating <sup>(1)</sup>**

Sym	Parameters/Condition	Unit	Absolute Max
Vbias	Bias Voltage (RF Input)	V	2
Ibias	Bias Current	mA	1
P <sub>in, max</sub>	CW RF Input Power (RF Input) <sup>(2)</sup>	dBm	+31
Tch	Max Channel Temperature	°C	+150
Tstg	Storage Temperature	°C	+150

Notes

1. Operation of this device above any one of these parameters may cause permanent damage
2. With the DC (typical bias) and RF applied to the device at board temperature, T<sub>b</sub> = 25° C

**Table 2. DC and RF Specifications**

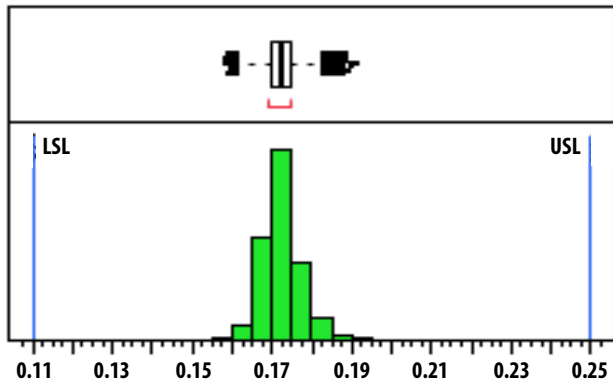
T<sub>A</sub> = 25° C, Freq = 24 GHz, V<sub>b</sub> = 1.5 V, Z<sub>in</sub> = Z<sub>out</sub> = 50 Ω unless otherwise specified

Symbol	Parameters / Condition	Unit	Min	Typical	Max
Ibias <sup>(1)</sup>	Bias Current	mA	0.11	0.17	0.25
I.L. <sup>(1)</sup>	Insertion Loss at 15 GHz at 24 GHz at 33 GHz	dB		0.3 0.5 0.7	
IRL <sup>(1)</sup>	Input Return Loss	dB		20	
ORL <sup>(1)</sup>	Output Return Loss	dB		20	
Dir <sup>(2)</sup>	Directivity at 15 GHz at 24 GHz at 33 GHz	dB		11 18 12	
Voffset <sup>(1,3)</sup>	Detector Output Offset Voltage	mV	45	61	75
Vdet <sup>(4)</sup>	Detector Output Voltage at +20 dBm	mV	0.90	1.07	1.22

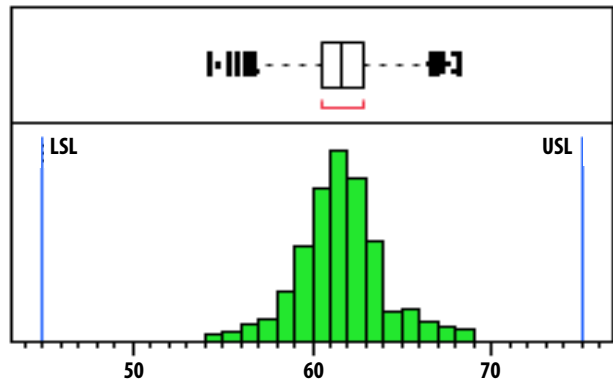
Notes

1. Measured data obtained from wafer-probing, losses from measurement system de-embedded from final data, V<sub>bias</sub> = 1.5 V applied through a broadband bias tee.
2. Measured by reversing the detector and applying RF power to the output port. Directivity is defined as the difference in dB between the power applied in the forward direction and the power required in the reverse direction to produce the same V<sub>det</sub> voltage.
3. Voffset is measured with RF input power turned off.
4. Vdet is measured with +20 dBm RF input power at 22 GHz.

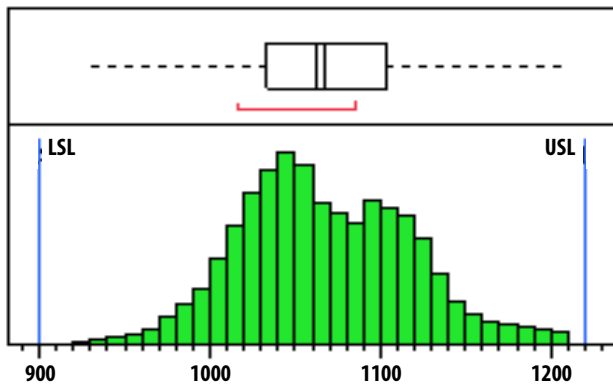
**Product Consistency Distribution Charts at 24 GHz, Vbias = 1.5 V**



Ibias: Mean = 0.17 mA, LSL = 0.11 mA, USL = 0.25 mA



Voffset: Mean = 61 mV, LSL = 45 mV, USL = 75 mV



Vdet\_On @ Pin = +20 dBm: Mean = 1.07 V, LSL = 0.9 V, USL = 1.22 V

Notes:  
 Distribution data sample sized is based on at least 36 Kpcs taken from MPV lots.  
 Future wafers allocated to this product may have nominal values anywhere between the upper and lower limits.

## VMMK-3313 Typical Performance

S-parameter data obtained using 300  $\mu\text{m}$  G-S-G probe substrate; bias was brought in via broadband bias tees. Power vs. Vdet data obtained using CPW PCB (Fig.8). Losses calibrated out to the package reference plane.  
 ( $T_A = 25^\circ\text{C}$ ,  $V_{\text{bias}} = 1.5\text{ V}$ ,  $I_{\text{bias}} = 0.14\text{ mA}$ ,  $Z_{\text{in}} = Z_{\text{out}} = 50\ \Omega$  unless otherwise specified)

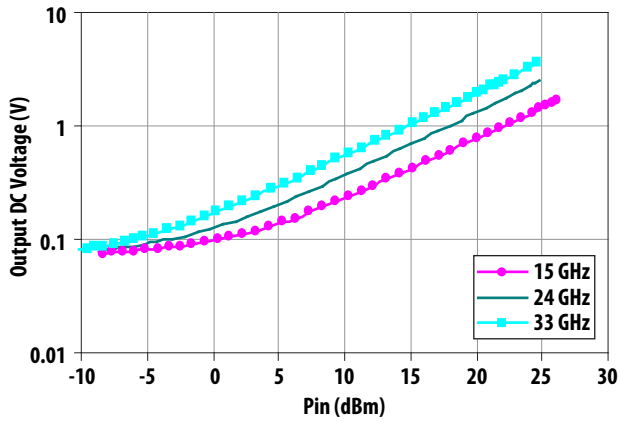


Figure 1. Vdet vs. Input Power

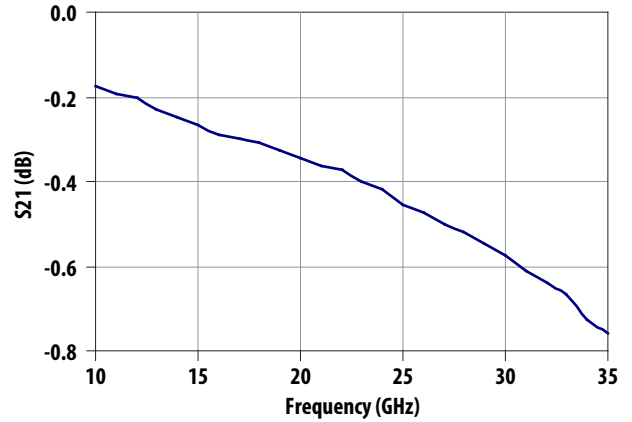


Figure 2. Insertion Loss vs. Frequency

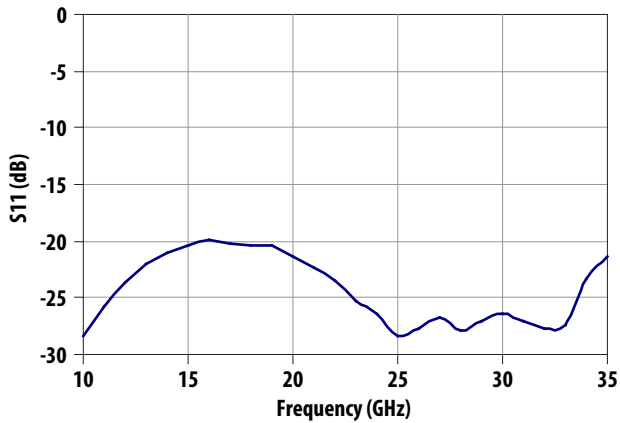


Figure 3. Input Return Loss

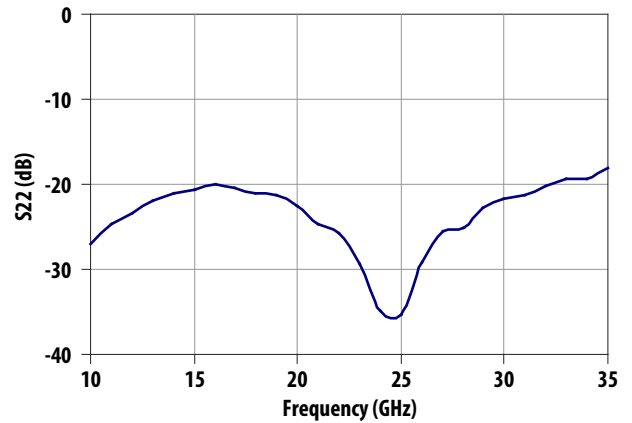


Figure 4. Output Return Loss

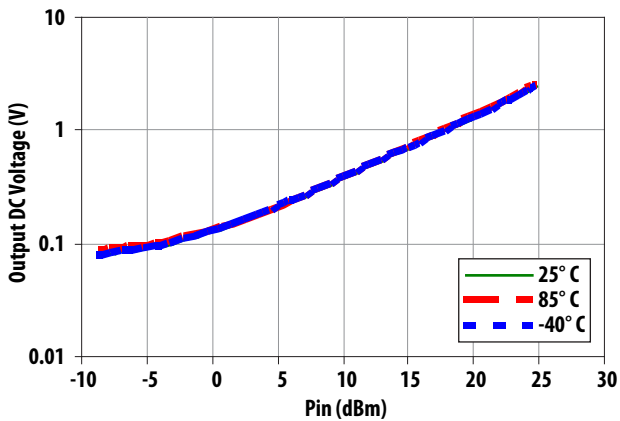


Figure 5. Pin vs. Vdet Over Temperature at 24 GHz

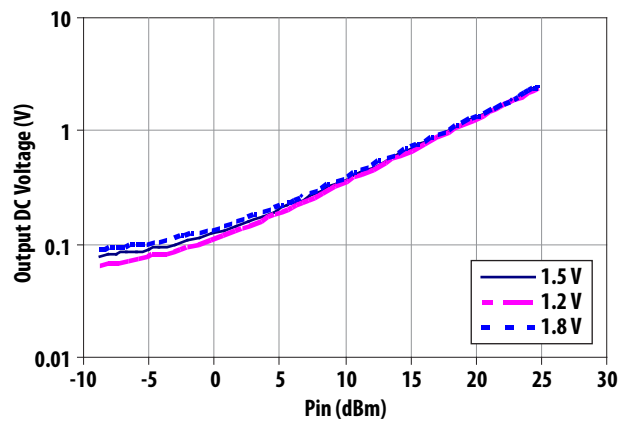


Figure 6. Pin vs. Vdet Over Vbias at 24 GHz

## Typical Scattering Parameters

Data obtained with 300  $\mu\text{m}$  G-S-G probing on 0.016 inch thick PCB substrate, broadband bias tees, losses calibrated out to the package reference plane.  $T_A = 25^\circ\text{C}$ ,  $Z_{in} = Z_{out} = 50\ \Omega$ .

Freq GHz	S11			S21			S12			S22		
	dB	Mag	Phase	dB	Mag	Phase	dB	Mag	Phase	dB	Mag	Phase
2.0	-16.143	0.156	-90.494	-0.192	0.978	-0.747	-0.186	0.979	-0.679	-16.016	0.158	-93.644
3.0	-19.760	0.103	-96.650	-0.132	0.985	-8.728	-0.124	0.986	-8.670	-19.659	0.104	-105.358
4.0	-22.639	0.074	-100.139	-0.128	0.985	-15.231	-0.116	0.987	-15.156	-22.441	0.076	-116.420
5.0	-25.368	0.054	-99.264	-0.122	0.986	-21.092	-0.115	0.987	-21.017	-25.083	0.056	-130.972
6.0	-28.427	0.038	-93.825	-0.126	0.986	-26.725	-0.126	0.986	-26.669	-27.453	0.042	-151.611
7.0	-31.502	0.027	-78.538	-0.139	0.984	-32.188	-0.129	0.985	-32.126	-29.736	0.033	-178.623
8.0	-32.918	0.023	-48.363	-0.145	0.983	-37.503	-0.144	0.984	-37.516	-30.201	0.031	146.185
9.0	-31.634	0.026	-16.396	-0.169	0.981	-42.803	-0.155	0.982	-42.811	-29.020	0.035	115.496
10.0	-28.336	0.038	1.025	-0.174	0.980	-48.135	-0.171	0.981	-48.095	-26.897	0.045	90.525
11.0	-25.713	0.052	6.348	-0.191	0.978	-53.426	-0.185	0.979	-53.345	-24.672	0.058	75.623
12.0	-23.583	0.066	7.497	-0.204	0.977	-58.602	-0.208	0.976	-58.544	-23.312	0.068	62.771
13.0	-22.015	0.079	7.691	-0.225	0.974	-63.871	-0.226	0.974	-63.782	-21.841	0.081	52.793
14.0	-21.100	0.088	7.152	-0.247	0.972	-69.068	-0.240	0.973	-69.014	-21.002	0.089	44.150
15.0	-20.464	0.095	5.699	-0.261	0.970	-74.298	-0.261	0.970	-74.185	-20.612	0.093	34.963
16.0	-19.837	0.102	4.621	-0.288	0.967	-79.432	-0.279	0.968	-79.412	-20.070	0.099	26.214
17.0	-20.229	0.097	4.889	-0.302	0.966	-84.664	-0.300	0.966	-84.646	-20.473	0.095	19.684
18.0	-20.427	0.095	5.722	-0.311	0.965	-89.942	-0.308	0.965	-89.871	-21.130	0.088	12.443
19.0	-20.346	0.096	4.424	-0.331	0.963	-95.142	-0.334	0.962	-95.072	-21.190	0.087	3.542
20.0	-21.391	0.085	7.308	-0.346	0.961	-100.462	-0.345	0.961	-100.384	-22.651	0.074	-0.777
21.0	-22.441	0.076	10.427	-0.361	0.959	-105.667	-0.355	0.960	-105.641	-24.716	0.058	-5.533
22.0	-23.491	0.067	10.306	-0.377	0.958	-110.947	-0.376	0.958	-110.951	-25.900	0.051	-11.559
23.0	-25.304	0.054	23.895	-0.401	0.955	-116.285	-0.401	0.955	-116.288	-29.473	0.034	-2.535
24.0	-26.448	0.048	41.694	-0.416	0.953	-121.674	-0.419	0.953	-121.646	-34.943	0.018	31.366
25.0	-28.427	0.038	51.641	-0.453	0.949	-127.022	-0.455	0.949	-127.007	-35.189	0.017	74.893
26.0	-27.787	0.041	75.394	-0.472	0.947	-132.447	-0.476	0.947	-132.366	-29.168	0.035	83.707
27.0	-26.707	0.046	90.267	-0.505	0.944	-137.920	-0.505	0.944	-137.910	-25.547	0.053	87.920
28.0	-27.872	0.040	108.771	-0.517	0.942	-143.371	-0.519	0.942	-143.334	-25.161	0.055	86.868
29.0	-27.131	0.044	110.745	-0.550	0.939	-148.819	-0.546	0.939	-148.784	-22.722	0.073	68.734
30.0	-26.430	0.048	123.049	-0.576	0.936	-154.323	-0.582	0.935	-154.356	-21.650	0.083	61.896
31.0	-27.171	0.044	141.654	-0.614	0.932	-160.111	-0.612	0.932	-160.110	-21.300	0.086	51.421
32.0	-27.702	0.041	157.497	-0.643	0.929	-165.730	-0.640	0.929	-165.797	-20.211	0.098	37.365
33.0	-27.412	0.043	175.942	-0.665	0.926	-171.312	-0.664	0.926	-171.290	-19.404	0.107	18.402
34.0	-23.414	0.068	-159.594	-0.722	0.920	-177.364	-0.715	0.921	-177.358	-19.437	0.107	-1.031
35.0	-21.351	0.086	-142.243	-0.726	0.920	176.755	-0.724	0.920	176.769	-18.062	0.125	-17.686
36.0	-19.164	0.110	-145.966	-0.812	0.911	170.964	-0.814	0.911	171.148	-17.329	0.136	-32.214
37.0	-16.815	0.144	-142.957	-0.866	0.905	164.889	-0.887	0.903	165.274	-16.340	0.152	-48.123
38.0	-15.080	0.176	-138.352	-1.004	0.891	159.328	-0.935	0.898	159.556	-15.396	0.170	-62.771
39.0	-14.239	0.194	-142.217	-1.047	0.886	153.991	-1.022	0.889	154.016	-14.624	0.186	-72.930
40.0	-13.011	0.224	-143.357	-1.124	0.879	148.264	-1.084	0.883	148.305	-13.936	0.201	-85.368

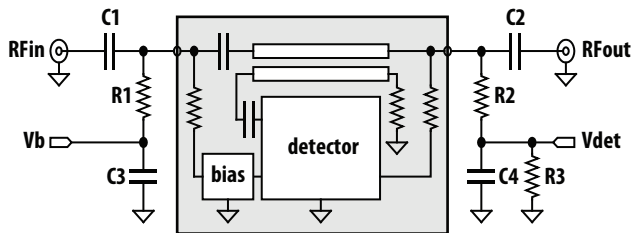
## VMMK-3313 Biasing Information

### Biasing and Operation

The VMMK-3313 is a 3 terminal device consisting of a “through” 50 ohm line connecting directly between the RF Input and RF Output ports and a directional coupler with a full wave detector that provides a DC output proportional to RF power input. As with any high frequency device, good grounding is required on the common port under the device for it to produce low loss in the “through” mode. A suggested PCB layout with appropriate grounding will be cover later in this application section.

With only 3 terminals available, the DC bias and detected voltage are internally DC coupled to the input and output terminals respectively. The key to successful operation of the VMMK-3313 is the use of low loss bias decoupling networks connected to both the RF Input and the RF Output ports. Figure 7 shows a simple biasing circuit.

The bias decoupling networks provide a low loss AC coupled RF path to the device, a means of biasing the device on the input, and a means of extracting the detected voltage on the output of the device. The detector needs 2 DC blocking caps, C1 and C2, on the input and output ports. This can be accomplished by printing coupled lines on the PCB or using SMT capacitors (ATC 600 series) with



Component	Description
C1, C2	0.2 pF to 0.4 pF (ATC 600 or printed coupled lines)
R1	$(V_b - 1.5) / 0.00014 \Omega$
R2	10 k $\Omega$
C3, C4	1 pF
R3	External load resistor (optional)

Figure 7. Biasing the VMMK-3313 Detector Module

values chosen for the frequency of operation. All SMT components are recommended to be no larger than 0402 size. Nominal bias voltage of 1.5 V or 0.14 mA is required for proper operation. Biasing on the input is by a way of a large value resistor R1. Its value can be computed using the following equation:

$$R1 = (V_b - 1.5) / 0.00014$$

where  $V_b$  is the supply voltage.

Detected DC voltage is extracted on the output by a way of a large value resistor R2, in the range of 10 k $\Omega$ . Bypassing capacitors C3 and C4 are needed to prevent RF influence on the dc lines. Suggested value for bypass capacitors is 1 pF.

At zero RF input power, and at 1.5 V supply bias, a nominal 63 mV offset voltage appears at the detected output port. The internal output source resistance for the detector is approximately 20 k $\Omega$ . Resistor R3 can be used as an external load resistor for the detector. Its value can be optimized for the desired  $V_{out}$  vs. RF input curve.

Figure 8 shows a VMMK-3313 characterization PCB used to obtain the  $V_{det}$  vs. Input Power characterization data from 15 to 33 GHz. For ease in broadband characterization, two external 45 MHz – 50 GHz Bias Networks (HP 11612B) were used.

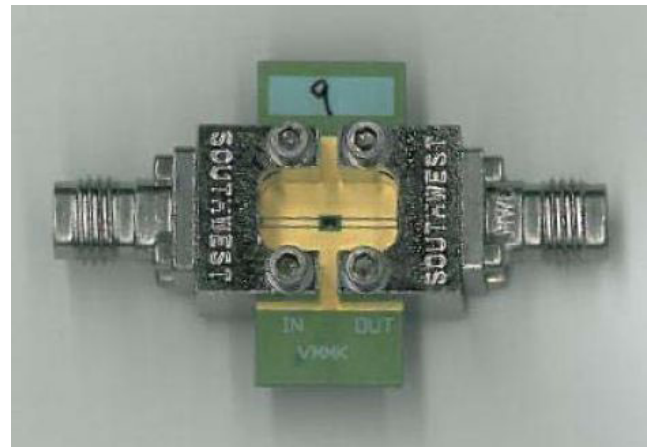


Figure 8. VMMK-3313 Characterization Board

## S Parameter Measurements

The S-parameters are measured on a 0.016 inch thick RO4003 printed circuit test board, using 300 μm G-S-G (ground signal ground) probes. Coplanar waveguide is used to provide a smooth transition from the probes to the device under test. The presence of the ground plane on top of the test board results in excellent grounding at the device under test. A combination of SOLT (Short – Open – Load – Thru) and TRL (Thru – Reflect – Line) calibration techniques are used to correct for the effects of the test board, resulting in accurate device S parameters.

## Package and Assembly Notes

For detailed description of the device package and assembly notes, please refer to Application Note 5378.

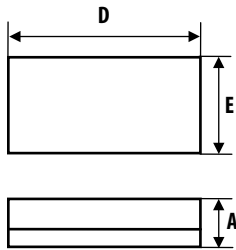
## ESD Precautions

Note: These devices are ESD sensitive. The following precautions are strongly recommended. Ensure that an ESD approved carrier is used when die are transported from one destination to another. Personal grounding is to be worn at all times when handling these devices. For more detail, refer to Avago Application Note A004R: Electrostatic Discharge Damage and Control.

## Ordering Information

Part Number	Devices Per Container	Container
VMMK-3313-BLKG	100	Antistatic Bag
VMMK-3313-TR1G	5000	7" Reel
VMMK-3313-TR2G	1000	7" Reel

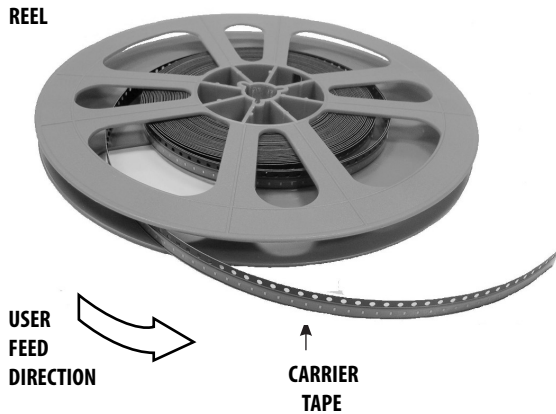
## Package Dimension Outline



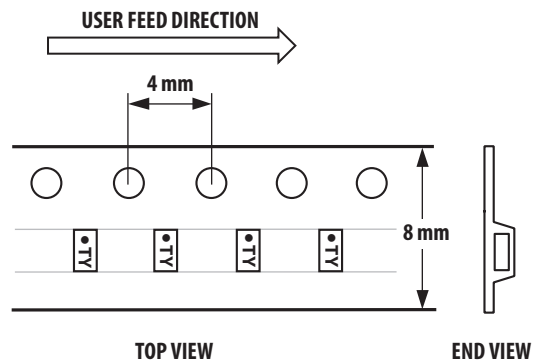
Dimensions Symbol	Min (mm)	Max (mm)
E	0.500	0.585
D	1.004	1.085
A	0.225	0.275

Note:  
All dimensions are in mm

## Reel Orientation

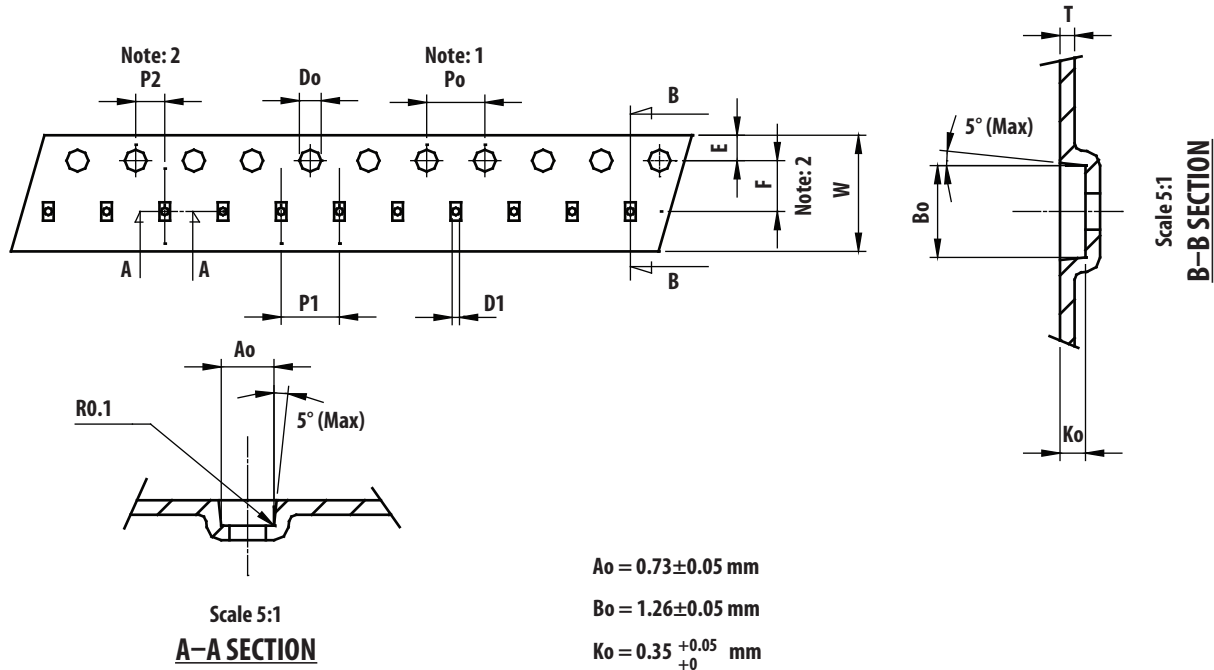


## Device Orientation



Notes:  
"T" = Device Code  
"Y" = Month Code

## Tape Dimensions



Unit: mm

Symbol	Spec.
K1	-
Po	4.0 ± 0.10
P1	4.0 ± 0.10
P2	2.0 ± 0.05
Do	1.55 ± 0.05
D1	0.5 ± 0.05
E	1.75 ± 0.10
F	3.50 ± 0.05
10Po	40.0 ± 0.10
W	8.0 ± 0.20
T	0.20 ± 0.02

Notice:

1. 10 Sprocket hole pitch cumulative tolerance is ±0.1 mm.
2. Pocket position relative to sprocket hole measured as true position of pocket not pocket hole.
3. Ao & Bo measured on a plane 0.3 mm above the bottom of the pocket to top surface of the carrier.
4. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
5. Carrier camber shall be not than 1 m per 100 mm through a length of 250 mm.

For product information and a complete list of distributors, please go to our web site: [www.avagotech.com](http://www.avagotech.com)

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